**Preferred Device** 

### **Silicon Controlled Rectifiers**

## **Reverse Blocking Thyristors**

Designed primarily for half-wave ac control applications, such as motor controls, heating controls and power supply crowbar circuits.

- Glass Passivated Junctions with Center Gate Fire for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Constructed for Low Thermal Resistance, High Heat Dissipation and Durability
- Blocking Voltage to 800 Volts
- 300 A Surge Current Capability
- Insulated Package Simplifies Mounting
- N Indicates UL Registered File #E69369
- Device Marking: Logo, Device Type, e.g., MCR225-8FP, Date Code

#### **MAXIMUM RATINGS** (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage(1)  (T <sub>J</sub> = -40 to +125°C, Sine Wave, 50 to 60 Hz, Gate Open)  MCR225–8FP  MCR225–10FP	VDRM, VRRM	600 800	Volts
On-State RMS Current ( $T_C = +70^{\circ}C$ )	I <sub>T</sub> (RMS)	25	Amps
(180° Conduction Angles)			
Peak Non–repetitive Surge Current (1/2 Cycle, Sine Wave 60 Hz, T <sub>C</sub> = +70°C)	ITSM	300	Amps
Circuit Fusing (t = 8.3 ms)	I <sup>2</sup> t	375	A <sup>2</sup> s
Forward Peak Gate Power $(T_C = +70^{\circ}C, \text{ Pulse Width } \leq 1.0  \mu\text{s})$	PGM	20	Watts
Forward Average Gate Power (T <sub>C</sub> = +70°C, t = 8.3 ms)	PG(AV)	0.5	Watt
Forward Peak Gate Current $(T_C = +70^{\circ}C, \text{ Pulse Width } \le 1.0  \mu\text{s})$	IGM	2.0	Amps
RMS Isolation Voltage (T <sub>A</sub> = 25°C, Relative Humidity ≤ 20%) (%)	V(ISO)	1500	Volts
Operating Junction Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-40 to +150	°C

<sup>(1)</sup> VDRM and VRRM for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



#### ON Semiconductor

http://onsemi.com

### ISOLATED SCRs (%) 25 AMPERES RMS 600 thru 800 VOLTS





ISOLATED TO-220 Full Pack CASE 221C STYLE 2

PIN ASSIGNMENT			
1	Cathode		
2	Anode		
3	Gate		

#### ORDERING INFORMATION

Device	Package	Shipping
MCR225-8FP	ISOLATED TO220FP	500/Box
MCR225-10FP	ISOLATED TO220FP	500/Box

**Preferred** devices are recommended choices for future use and best overall value.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.5	°C/W
Thermal Resistance, Case to Sink	$R_{\theta}CS$	2.2 (typ)	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	TL	260	°C

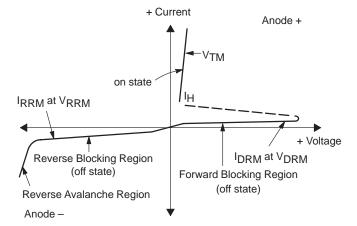
### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•		•		•
Peak Repetitive Forward or Reverse Blocking Current $(V_D = Rated \ V_{DRM}, \ V_{RRM}; \ Gate \ Open)$ $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$	IDRM, IRRM	_	_	10 2	μA mA
ON CHARACTERISTICS	•				•
Peak Forward On–State Voltage <sup>(1)</sup> (I <sub>TM</sub> = 50 A)	Vтм		_	1.8	Volts
Gate Trigger Current (Continuous dc) (V <sub>AK</sub> = 12 Vdc, R <sub>L</sub> = 100 Ohms)	lGT		_	40	mA
Gate Trigger Voltage (Continuous dc) (V <sub>AK</sub> = 12 Vdc, R <sub>L</sub> = 100 Ohms)	V <sub>GT</sub>		0.8	1.5	Volts
Gate Non-Trigger Voltage (V <sub>AK</sub> = 12 Vdc, R <sub>L</sub> = 100 Ohms, T <sub>J</sub> = 125°C)	V <sub>GD</sub>	0.2	_	_	Volts
Holding Current (VAK = 12 Vdc, Initiating Current = 200 mA, Gate Open)	lн	_	20	40	mA
Turn-On Time (I <sub>TM</sub> = 25 A, I <sub>GT</sub> = 40 mAdc)	<sup>t</sup> gt	_	1.5	_	μs
Turn-Off Time (V <sub>DRM</sub> = Rated Voltage) (I <sub>TM</sub> = 25 A, I <sub>R</sub> = 25 A) (I <sub>TM</sub> = 25 A, I <sub>R</sub> = 25 A, T <sub>J</sub> = 125°C)	<sup>t</sup> q		15 35		μѕ
DYNAMIC CHARACTERISTICS	-				
Critical Rate-of-Rise of Off-State Voltage (Gate Open, V <sub>D</sub> = Rated V <sub>DRM</sub> , Exponential Waveform)	dv/dt	_	100	_	V/µs

<sup>(1)</sup> Pulse Test: Pulse Width = 1.0 ms, Duty Cycle  $\leq$  2%.

### **Voltage Current Characteristic of SCR**

Symbol	Parameter
VDRM	Peak Repetitive Off State Forward Voltage
IDRM	Peak Forward Blocking Current
VRRM	Peak Repetitive Off State Reverse Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
$V_{TM}$	Peak on State Voltage
lΗ	Holding Current



#### **TYPICAL CHARACTERISTICS**

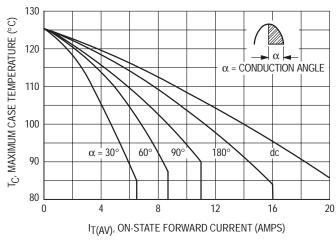


Figure 1. Average Current Derating

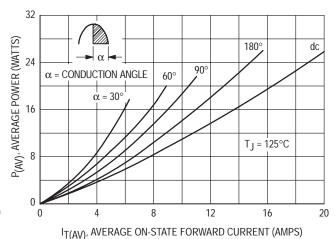
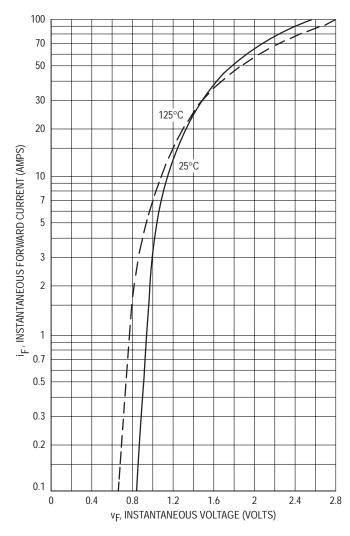


Figure 2. Maximum On-State Power Dissipation



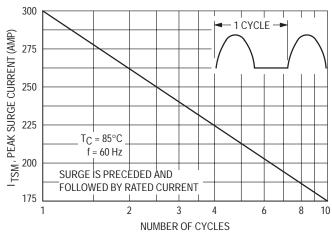


Figure 3. Maximum Forward Voltage

Figure 4. Maximum Non-Repetitive Surge Current

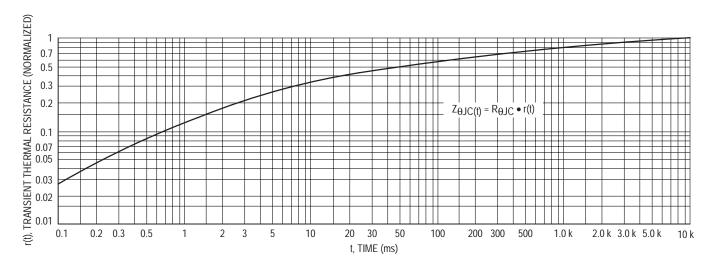


Figure 5. Thermal Response

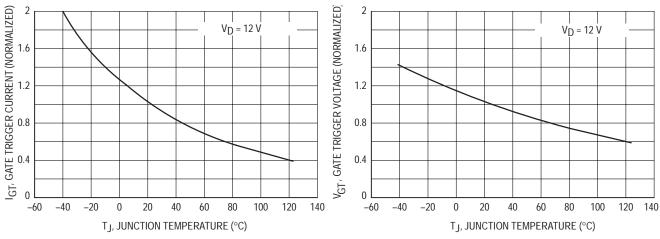


Figure 6. Typical Gate Trigger Current versus Temperature

Figure 7. Typical Gate Trigger Voltage versus Temperature

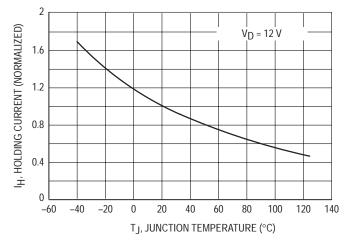
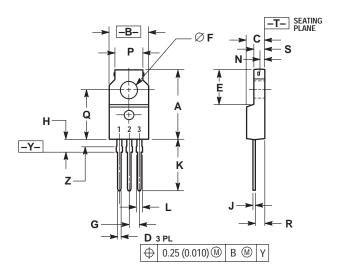


Figure 8. Typical Holding Current versus Temperature

#### **PACKAGE DIMENSIONS**

#### ISOLATED TO-220 Full Pack

CASE 221C-02 ISSUE C



- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: INCH.

  3. LEAD DIMENSIONS UNCONTROLLED WITHIN DIMENSION Z.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.680	0.700	17.28	17.78
В	0.388	0.408	9.86	10.36
С	0.175	0.195	4.45	4.95
D	0.025	0.040	0.64	1.01
Ε	0.340	0.355	8.64	9.01
F	0.140	0.150	3.56	3.81
G	0.100 BSC		2.54 BSC	
Н	0.110	0.155	2.80	3.93
J	0.018	0.028	0.46	0.71
K	0.500	0.550	12.70	13.97
L	0.045	0.070	1.15	1.77
N	0.049		1.25	
Р	0.270	0.290	6.86	7.36
Q	0.480	0.500	12.20	12.70
R	0.090	0.120	2.29	3.04
S	0.105	0.115	2.67	2.92
Z	0.070	0.090	1.78	2.28

STYLE 2: PIN 1. CATHODE 2. ANODE 3. GATE



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